

## P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (Typ)
- 60	0.085 at V <sub>GS</sub> = - 10 V	- 5	34
	0.100 at V <sub>GS</sub> = - 4.5 V	- 4	

### FEATURES

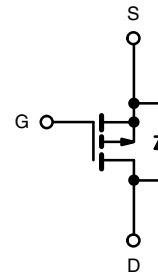
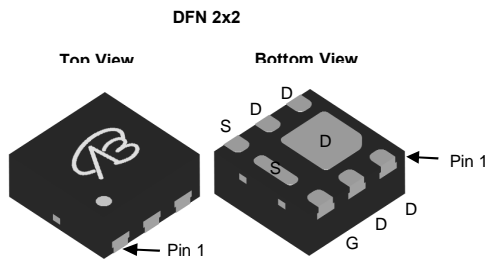
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- High Side Switch for Full Bridge Converter
- DC/DC Converter for LCD Display



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise note)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 60	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	- 5	A
	T <sub>C</sub> = 100 °C	- 4	
Pulsed Drain Current	I <sub>DM</sub>	- 15	
Avalanche Current, Single Pulse	I <sub>AS</sub>	- 22	mJ
Repetitive Avalanche Energy, Single Pulse <sup>a</sup>	E <sub>AS</sub>	24.2	
Power Dissipation	T <sub>C</sub> = 25 °C	38.5 <sup>c</sup>	W
	T <sub>A</sub> = 25 °C	2.3 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	t ≤ 10 s	R <sub>thJA</sub>	17	21	°C/W
	Steady State		45	55	
Maximum Junction-to-Case		R <sub>thJC</sub>	2.7	3.25	

Notes:

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.
- Based up on T<sub>C</sub> = 25 °C.

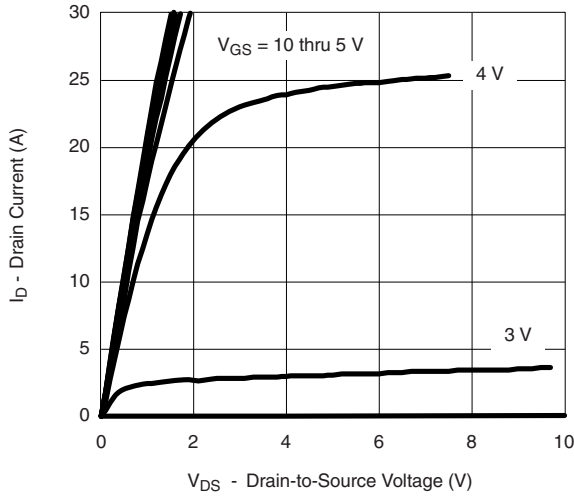
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise note)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			- 50	
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			- 125	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	- 20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		0.085		$\Omega$
		$V_{GS} = -10\text{ V}, I_D = -10\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.127		
		$V_{GS} = -10\text{ V}, I_D = -10\text{ A}, T_J = 150\text{ }^\circ\text{C}$		0.170		
		$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		0.100		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -10\text{ A}$		22		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		1000		$\text{pF}$
Output Capacitance	$C_{oss}$			130		
Reverse Transfer Capacitance	$C_{rss}$			90		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		30	40	$\text{nC}$
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			4.5		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			7		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		7		$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = -30\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong -19\text{ A}, V_{GEN} = -10\text{ V}, R_g = 2.5\text{ }\Omega$		8	15	ns
Rise Time <sup>c</sup>	$t_r$			9	15	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			65	100	
Fall Time <sup>c</sup>	$t_f$			30	45	
<b>Drain-Source Body Diode and Characteristics</b> ( $T_C = 25\text{ }^\circ\text{C}$ ) <sup>b</sup>						
Continuous Current	$I_S$				- 5	A
Pulsed Current	$I_{SM}$				- 15	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = -19\text{ A}, V_{GS} = 0\text{ V}$		-1	-1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = -19\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		41	61	ns

Notes:

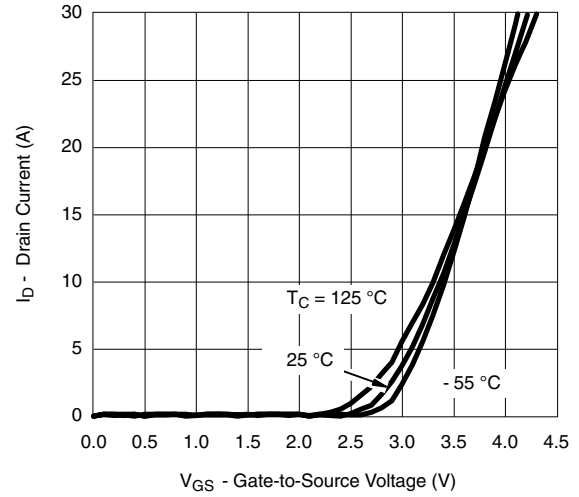
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

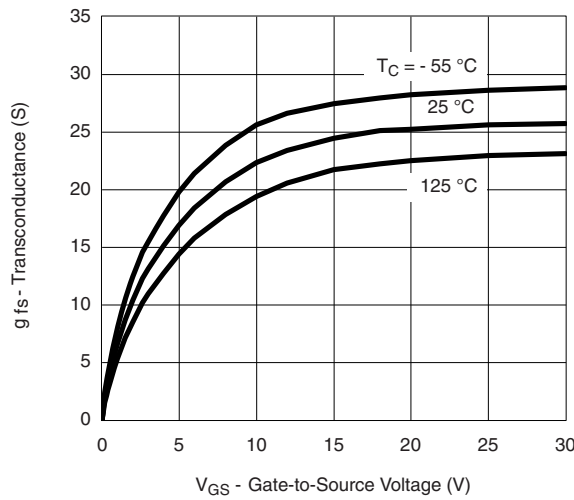
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



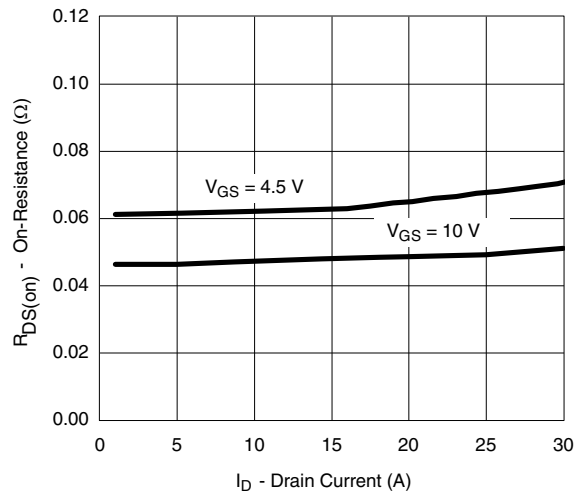
**Output Characteristics**



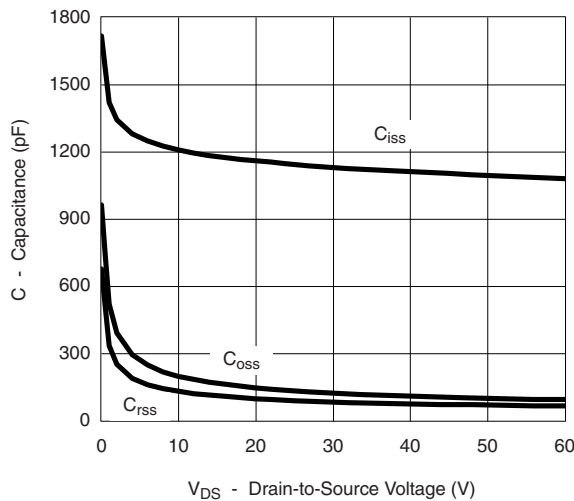
**Transfer Characteristics**



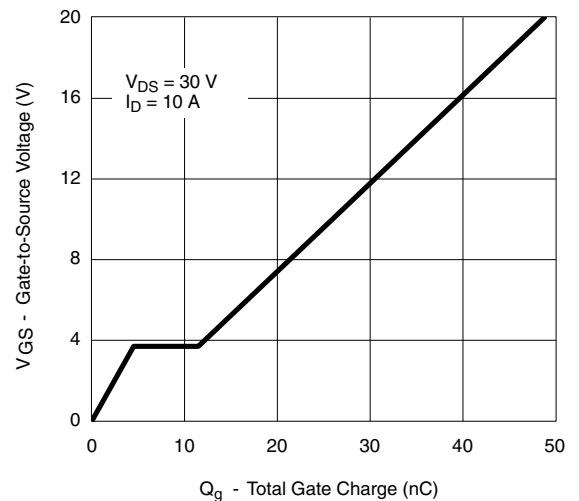
**Transconductance**



**On-Resistance vs. Drain Current**

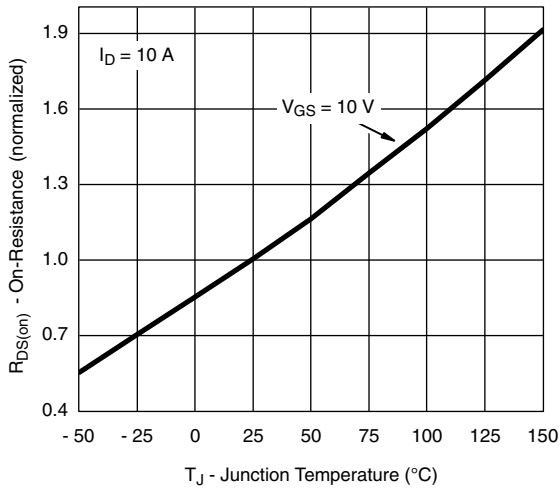


**Capacitance**

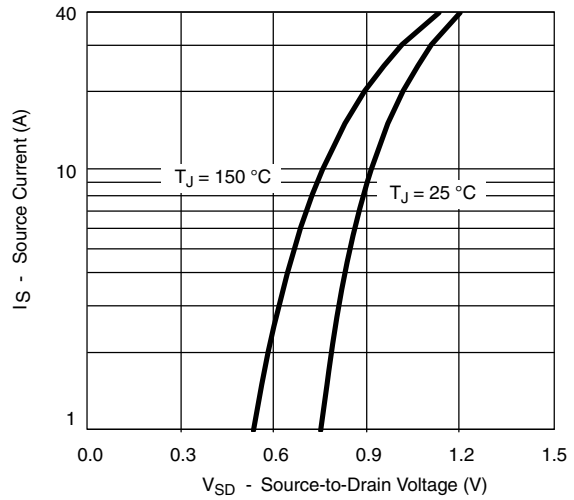


**Gate Charge**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

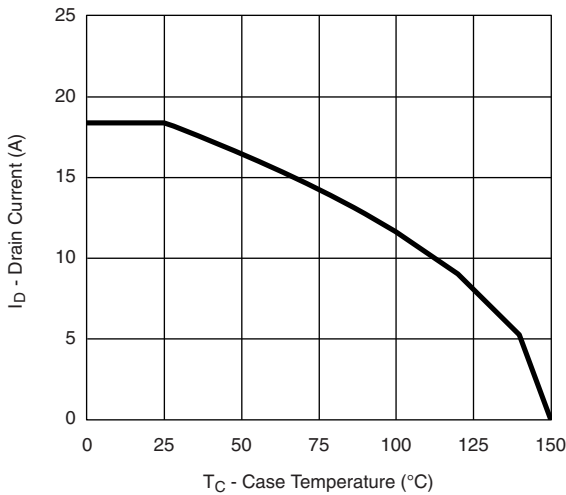


On-Resistance vs. Junction Temperature

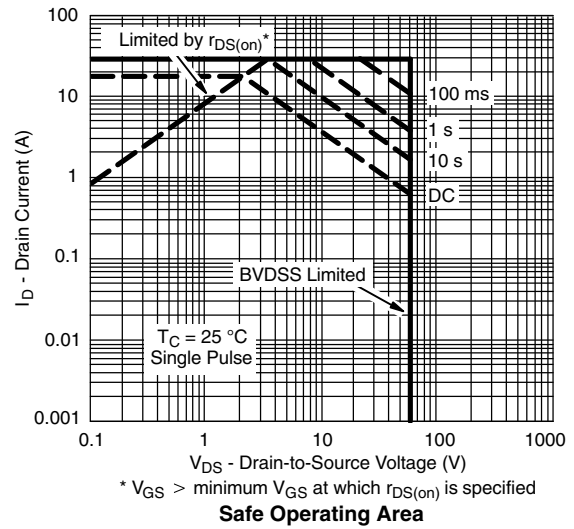


Source-Drain Diode Forward Voltage

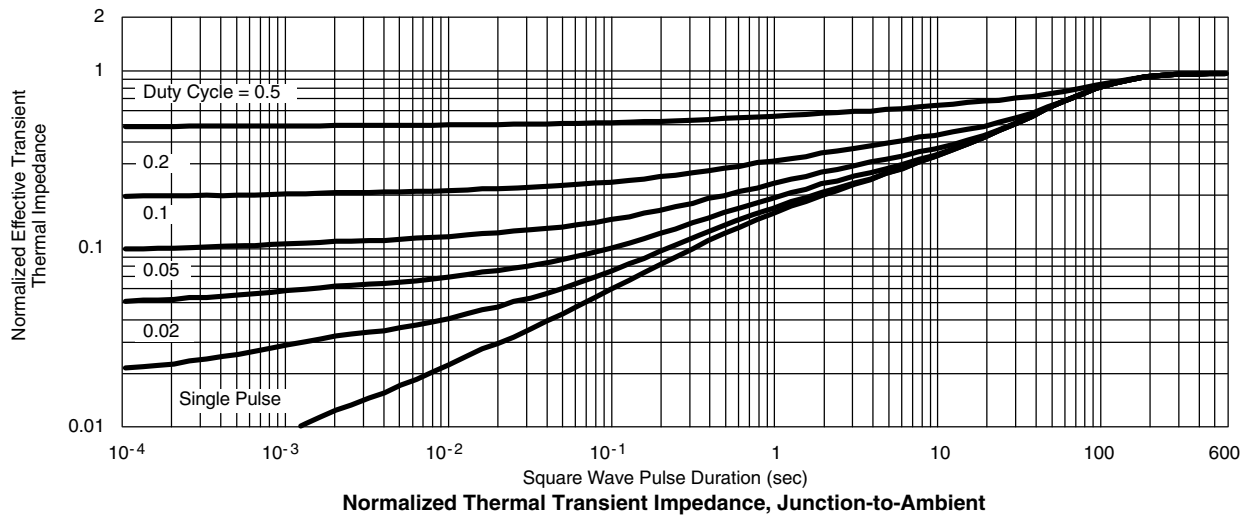
**THERMAL RATINGS**



Maximum Drain Current vs. Case Temperature

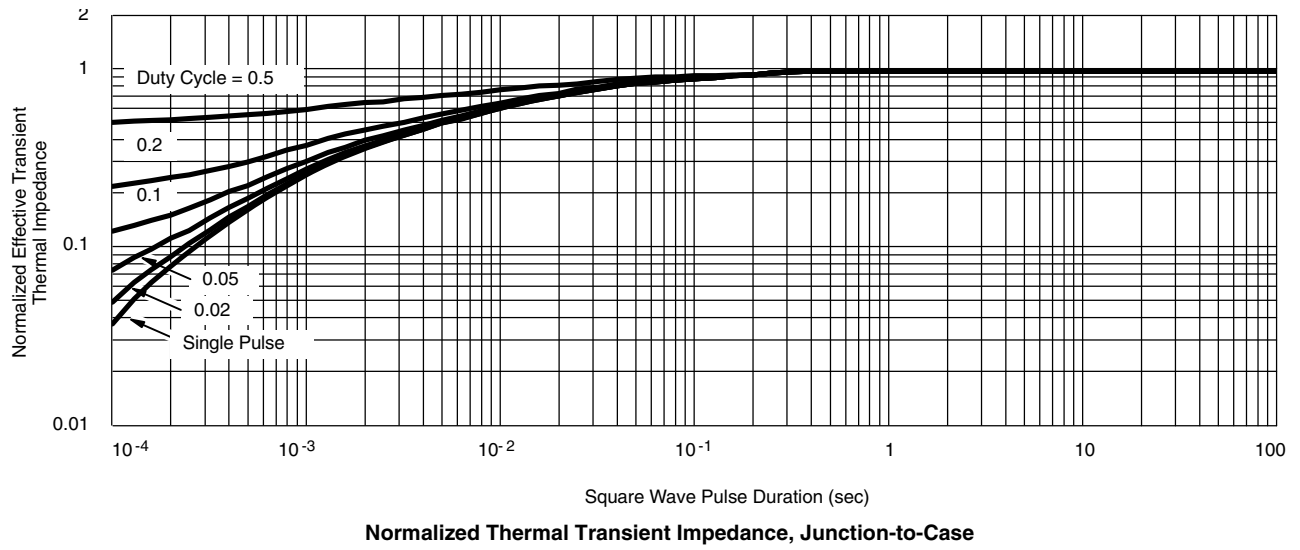


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified  
Safe Operating Area

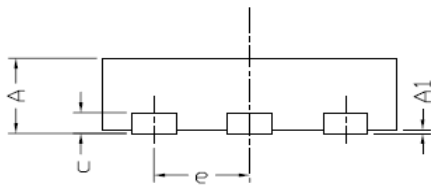
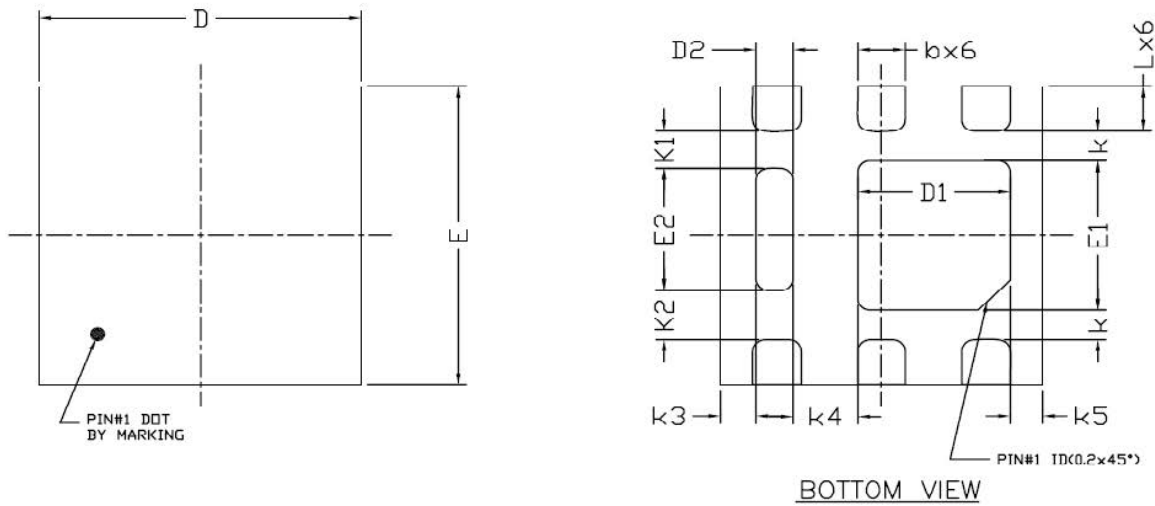


Normalized Thermal Transient Impedance, Junction-to-Ambient

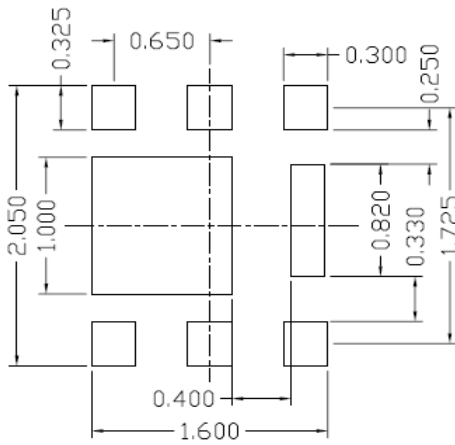
**THERMAL RATINGS**



DFN2x2 \_6L\_EP1\_S PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



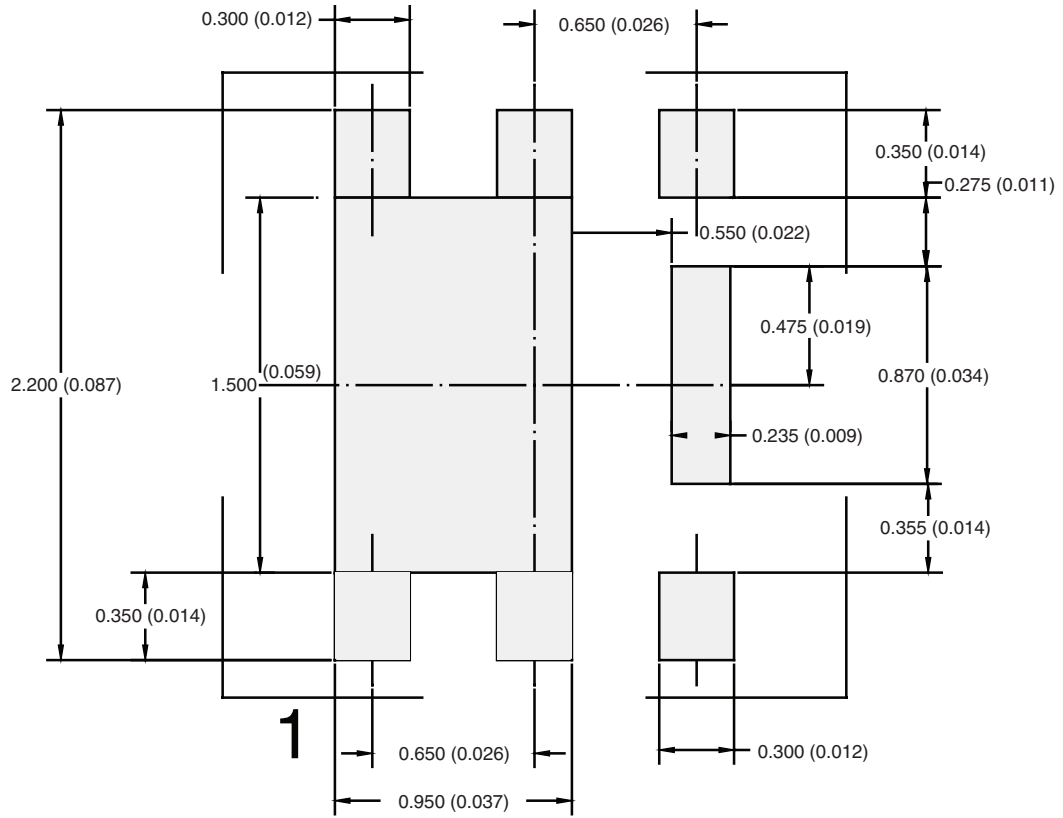
UNIT: mm

NOTE

1. CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	—	0.05	0.000	—	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.152 REF			0.006 REF		
D	1.90	2.00	2.10	0.075	0.079	0.083
D1	0.85	0.95	1.05	0.033	0.037	0.041
D2	0.13	0.23	0.33	0.005	0.009	0.013
E	1.90	2.00	2.10	0.075	0.079	0.083
E1	0.90	1.00	1.10	0.035	0.039	0.043
E2	0.72	0.82	0.92	0.028	0.032	0.036
e	0.65 BSC			0.026 BSC		
K	0.20 BSC			0.008 BSC		
K1	0.25 BSC			0.010 BSC		
K2	0.33 BSC			0.013 BSC		
K3	0.22 BSC			0.009 BSC		
K4	0.40 BSC			0.016 BSC		
K5	0.20 BSC			0.008 BSC		
L	0.25	0.30	0.35	0.010	0.012	0.014

RECOMMENDED PAD LAYOUT FOR DFN2X2



Dimensions in mm/(Inches)

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